

Description

The AU1271D3 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU1271D3 complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small lead-free SOD-323 package. The small size and high ESD surge protection make AU1271D3 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Ultra low leakage: nA level
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 75A (8/20 μs)
- RoHS Compliant

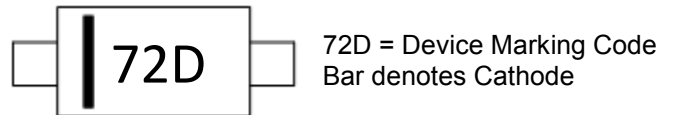
Mechanical Characteristics

- Package: SOD-323
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

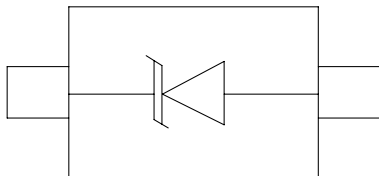
Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks, Desktops, Servers
- Portable Instrumentation
- Laser Diode Protection

Marking Information



Dimensions and Pin Configuration



SOD-323 (Top View)

Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AU1271D3	3000/Tape & Reel	7 inch

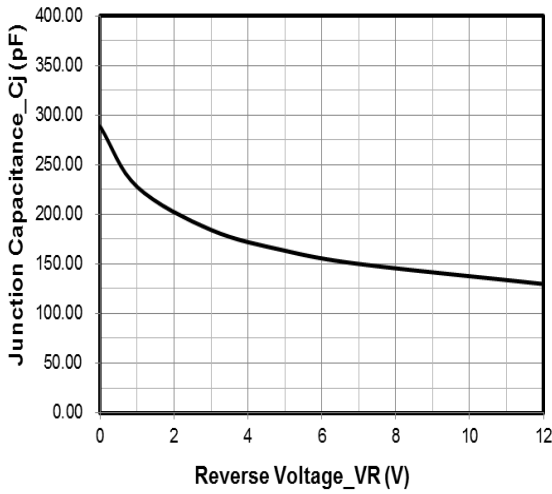
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	1875	W
Peak Pulse Current (8/20 μs)	Ipp	75	A
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

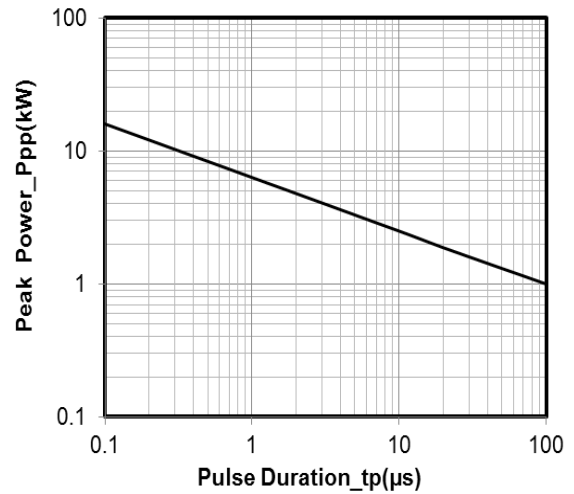
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3		17.8	V	$I_T = 1\text{mA}$
Reverse Leakage Current	I _R			0.2	μA	VRWM = 12V
Forward Voltage	V _F		1.0	1.2	V	I _F = 10mA
Clamping Voltage	V _C			18	V	I _{PP} = 10A (8 x 20 μs pulse)
Clamping Voltage	V _C			25	V	I _{PP} = 75A (8 x 20 μs pulse)
Junction Capacitance	C _J			300	pF	V _R = 0V, f = 1MHz

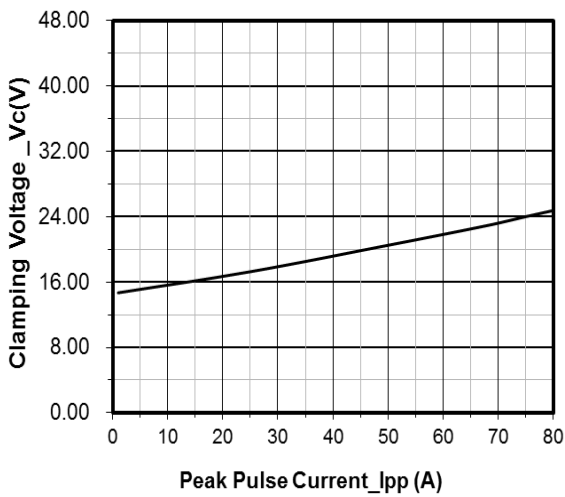
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



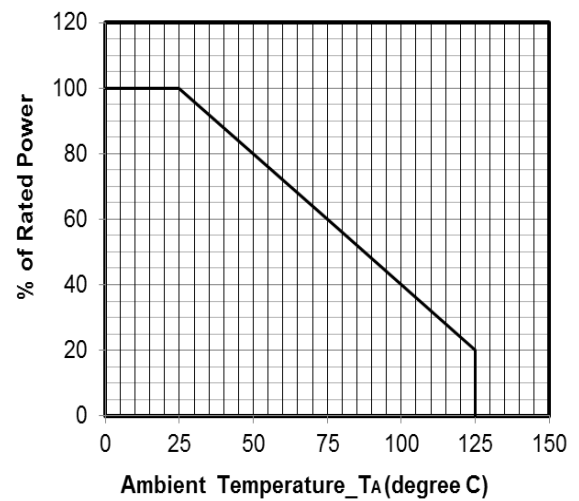
Junction Capacitance vs. Reverse Voltage



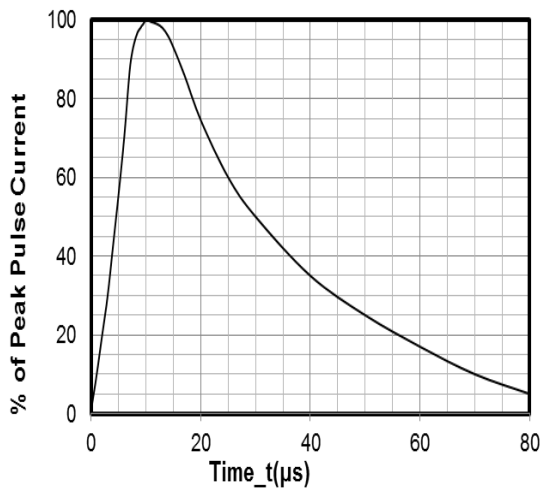
Peak Pulse Power vs. Pulse Time



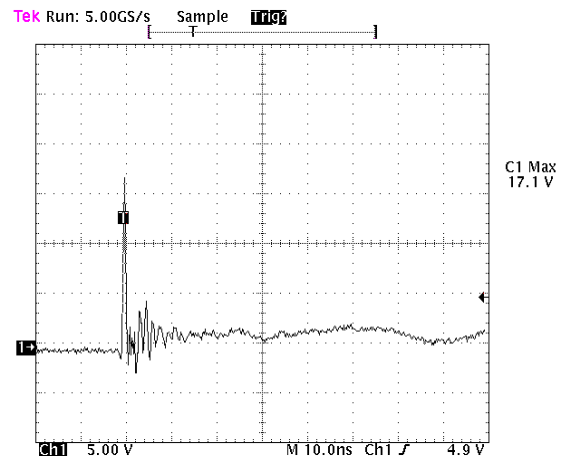
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

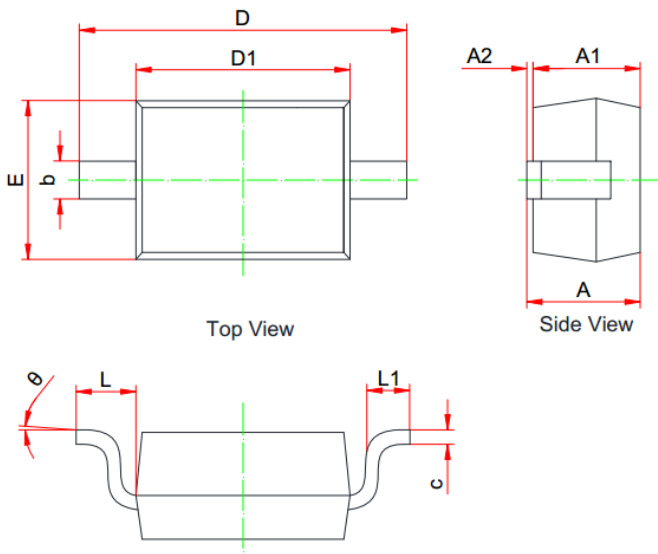


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

+8 kV Contact per IEC61000-4-2

SOD-323 Package Outline Drawing



SYM	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Theta	0°	--	8°

Suggested Land Pattern



Unit: mm

Contact Information

Applied Power Microelectronics Co., Ltd.

Website: <http://www.appliedpowermicro.com>

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606